

DB751S-40

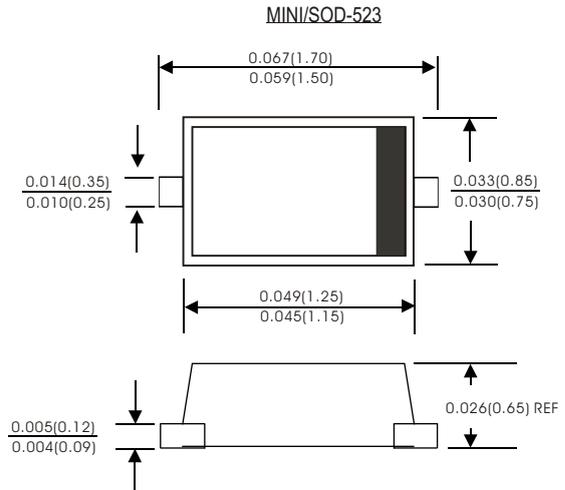
CHIP SCHOTTKY BARRIER DIODES

FEATURES:

- Small surface mounting type
- Low reverse current and low forwards voltage
- High reliability

MECHANICAL DATA

Case: Molded plastic, JEDEC SOD-523 / MINI SMA
 Terminals: Solder Plated, solderable per MIL-STD-750, Method 2026
 Polarity : Any
 Mounting Position: Any
 Weight: 0.04g



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25° C ambient temp. unless otherwise specified.
 Single phase, half sine wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20 %.

Characteristic	Symbol	DB751S-40	Units
Maximum recurrent peak reverse voltage	V_{RRM}	40	Volts
Maximum RMS voltage	V_{RMS}	28	Volts
Maximum DC voltage	V_{DC}	40	Volts
Maximum average forward rectified current at $T_a=25^\circ C$	$I_{(AV)}$	30	mA
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	200	mA
Maximum instantaneous forward voltage drop per leg at 1.0mA (NOTE 2)	V_F	0.37	Volts
Maximum instantaneous reverse current at $V_R=30V$ (NOTE 2) $T_a=25^\circ C$	I_R	0.5	μA
Typical junction (NOTE 1)	C_J	2	PF
Operating temperature range	T_J	125	$^\circ C$
storage temperature range	T_{stg}	-55 to +125	$^\circ C$

NOTES:
 (1) Measured at 1.0 MHz and applied reverse of 1.0 Volts
 (2) Pulse test : 300us pulse width, 1% duty cycle

RATING AND CHARACTERISTIC CURVES DB751S-40

FIG.1- TYPICAL REVERSE CHARACTERISTICS

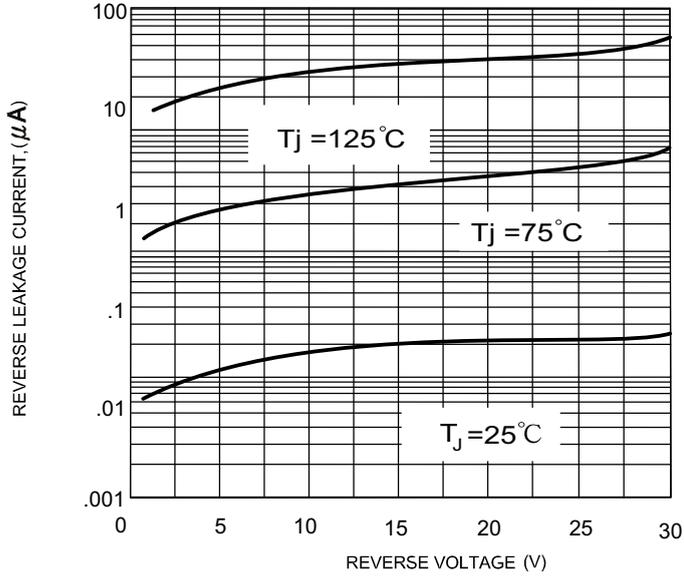


FIG.2 - TYPICAL FORWARD CHARACTERISTICS

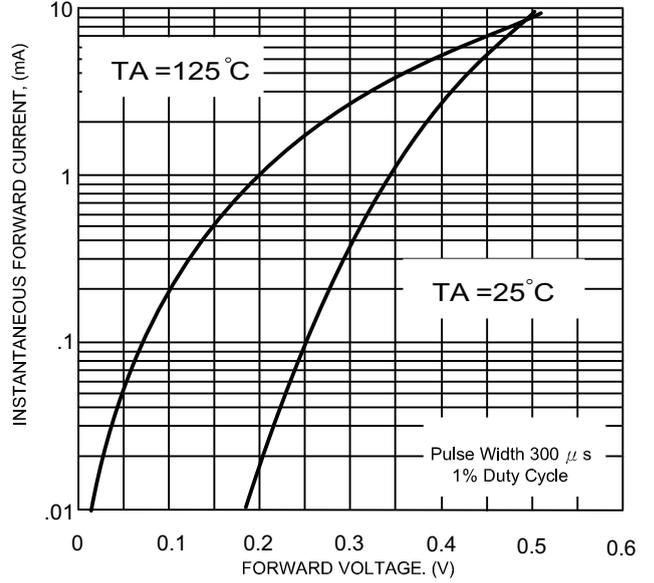


FIG.3- TYPICAL CAPACITANCE

